

U.S. Patent Application Serial No. 10/699,832
Amendment filed July 23, 2007
Reply to OA dated April 25, 2007

AMENDMENTS TO THE CLAIMS:

Please amend claim 1, as follows. This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A substrate for an electronic-optical united device being a component of an electronic-optical united device mixedly incorporating an electronic device such as an LSI and an optical device such as an LED and a laser diode, comprising ~~a monocrystalline silicon substrate being~~ an SOI substrate ~~including~~ that is a monocrystalline silicon substrate, the SOI substrate comprising:

one area formed with the electronic device; and

another area locally located and formed with the ~~electronic~~ optical device, comprising:

a layer of silicon carbide metamorphosed by locally carbonizing the corresponding area ~~in~~ of a surface the SOI substrate; and

a layer of monocrystalline gallium nitride grown on said layer of silicon carbide.

Claim 2 (Canceled).

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Claim 3 (Previously Presented): A substrate for an electronic-optical united device according to claim 1, said one area further comprising:

a layer of silicon nitride formed on the SOI substrate.

Claim 4 (Previously Presented): A substrate for an electronic-optical united device according to claim 1, said one area further comprising:

a layer of silicon oxide formed on the SOI substrate.

Claims 5-11 (Canceled).

Claim 12 (Previously Presented): A substrate for an electronic-optical united device according to claim 3, said one area further comprising:

a layer of polycrystalline gallium nitride grown on the layer of silicon nitride.

Claim 13 (Previously Presented): A substrate for an electronic-optical united device according to claim 4, said one area further comprising:

a layer of polycrystalline gallium nitride grown on the layer of silicon oxide.